PCT

INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification 6 :		(11) International Publication Number: **WO 95/30924**
G02F 1/31	**A1**	(43) International Publication Date: 16 November 1995 (16.11.95)

(21) International Application Number: PCT/US95/05358

(22) International Filing Date: 1 May 1995 (01.05.95)

(30) Priority Data:
08/238,750　　5 May 1994 (05.05.94)　　US

(60) Parent Application or Grant
(63) Related by Continuation
US　　　　　　　　　　08/238,750 (CIP)
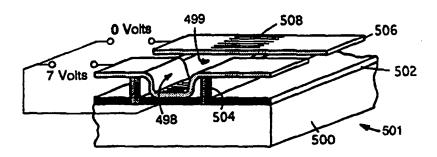Filed on　　　　　　5 May 1994 (05.05.94)

(71) Applicant (for all designated States except US): ETALON, INC. [US/US]; 33 Hanson Street, Boston, MA 02118 (US).

(72) Inventor; and
(75) Inventor/Applicant (for US only): MILES, Mark, W. [US/US]; 33 Hanson Street, Boston, MA 02118 (US).

(74) Agent: FEIGENBAUM, David, L.; Fish & Richardson P.C., 225 Franklin Street, Boston, MA 02110-2804 (US).

(81) Designated States: CA, CN, JP, KR, MX, US, European patent (AT, BE, CH, DE, DK, ES, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).

Published
With international search report.

(54) Title: VISIBLE SPECTRUM MODULATOR ARRAYS

(57) Abstract

　　Light in the visible spectrum is modulated using an array of modulation elements (501), and control circuitry connected to the array for controlling each of the elements having a surface (506) which is caused to exhibit a predetermined impedance characteristic to particular frequencies of light. The amplitude of light delivered by each of the modulation elements is controlled independently by pulse code modulation. Each modulation element has a deformable portion (508) held under tensile stress, and the control circuitry controls the deformation of the deformable portion. Each deformable element has a deformation mechanism and an optical portion independently imparting to the element respectively a controlled deformation characteristic and a controlled modulation characteristic. The deformable modulation element may be a non-metal. The elements are made by forming a sandwich of two layers and a sacrificial layer between them, the sacrificial layer having a thickness related to the final cavity dimension, and using chemical (e.g., water) or a plasma based etch process to remove the sacrificial layer.

- 1 -

VISIBLE SPECTRUM MODULATOR ARRAYS
Background

5   This is a continuation-in-part of United States
Patent Application Serial Number 08/238,750, filed May 5,
1994, which is a continuation-in-part of Serial No.
08/032,711, filed March 17, 1993.
          This invention relates to visible spectrum
10 (including ultra-violet and infrared) modulator arrays.
          Visible spectrum modulator arrays, such as backlit
LCD computer screens, have arrays of electro-optical
elements corresponding to pixels. Each element may be
electronically controlled to alter light which is aimed
15 to pass through the element. By controlling all of the
elements of the array, black and white or, using
appropriate elements, color images may be displayed.
Non-backlit LCD arrays have similar properties but work
on reflected light. These and other types of visible
20 spectrum modulator arrays have a wide variety of other
uses.

Summary of the Invention

          In general, in one aspect, the invention features
modulation of light in the visible spectrum using an
25 array of modulation elements, and control circuitry
connected to the array for controlling each of the
modulation elements independently, each of the modulation
elements having a surface which is caused to exhibit a
predetermined impedance characteristic to particular
30 frequencies of light.
          Implementations of the invention may include the
following features. The surface may include antennas
configured to interact with selected frequencies of
light, or the surface may be a surface of an interference

- 2 -

cavity. The impedance characteristic may be reflection
of particular frequencies of light, or transmission of
particular frequencies of light. Each of the modulation
elements may be an interference cavity that is deformable
5 to alter the cavity dimension. The interference cavity
may include a pair of cavity walls (e.g., mirrors)
separated by a cavity dimension. One of the mirrors may
be a broadband mirror and the other of the mirrors may be
a narrow band mirror. Or both of the mirrors may be
10 narrow band mirrors, or both of the mirrors may be broad
band, non-metallic mirrors. The cavity may have a cavity
dimension that renders the cavity resonant with respect
to light of the frequency defined by the spectral
characteristics of the mirrors and intrinsic cavity
15 spacing in an undeformed state. One of the mirrors may
be a hybrid filter. One (or both) of the walls may be a
dielectric material, a metallic material, or a composite
dielectric/metallic material. The cavity may be
deformable by virtue of a wall that is under tensile
20 stress. The control circuitry may be connected for
analog control of the impedance to light of each element.
The analog control may be control of the degree of
deformity of the deformable wall of the cavity.

        The predetermined impedance characteristic may
25 include reflection of incident electromagnetic radiation
in the visible spectrum, e.g., the proportion of incident
electromagnetic radiation of a given frequency band that
is, on average, reflected by each of the modulation
elements. The modulation element may be responsive to a
30 particular electrical condition to occupy either a state
of higher reflectivity or a state of lower reflectivity,
and the control circuitry may generate a stream of pulses
having a duty cycle corresponding to the proportion of
incident radiation that is reflected and places the
35 modulation element in the higher state of reflectivity

- 3 -

during each the pulse and in the lower state of
reflectivity in the intervals between the pulses. The
characteristic may include emission of electromagnetic
radiation in the visible spectrum. The characteristic
5 may include the amount of electromagnetic radiation in
the visible spectrum that is emitted, on average, by the
antennas. The characteristic may be incident
electromagnetic radiation in the-visible-spectrum. The
modulation elements may include three sub-elements each
10 associated with one of three colors of the visible
spectrum. The modulation element may be responsive to a
particular electrical condition to occupy either a state
of higher transmissivity or a state of lower
transmissivity, and the control circuitry may generate a
15 stream of pulses having a duty cycle corresponding to the
proportion of incident radiation that is transmitted and
places the modulation element in the higher state of
transmissivity during each the pulse and in the lower
state of transmissivity in the intervals between the
20 pulses. The characteristic may include the proportion of
incident electromagnetic radiation of a given frequency
band that is, on average, transmitted by each of the
modulation elements.

       The visible spectrum may include ultraviolet
25 frequencies, or infrared frequencies.

       In general, in another aspect of the invention,
the control circuitry may be connected to the array for
controlling the amplitude of light delivered by each of
the modulation elements independently by pulse code
30 modulation.

       In general, in another aspect, the invention
features a modulation element having a deformable portion
held under tensile stress, and control circuitry
connected to control the deformation of the deformable
35 portion.

- 4 -

Implementations of the invention may include the following features. The modulation element may be self-supporting. or held on separate supports. The deformable portion may be a rectangular membrane supported along two opposite edges by supports which are orthogonal to the membrane. The deformable portion, under one mode of control by the control circuitry, may be collapsed onto a wall of the cavity. The control circuitry controls the deformable portion by signals applied to the modulation element, and the deformation of the control portion may be subject to hysteresis with respect to signals applied by the control circuitry.

In general, in another aspect, the invention features modulating light in the visible spectrum using a deformable modulation element having a deformation mechanism and an optical portion, the deformation mechanism and the optical portion independently imparting to the element respectively a controlled deformation characteristic and a controlled modulation characteristic.

Implementations of the invention may include the following features. The deformation mechanism may be a flexible membrane held in tensile stress, and the optical portion may be formed on the flexible membrane. The optical portion may be a mirror. The mirror may have a narrow band, or a broad band, or include a hybrid filter.

In general, in another aspect, the invention broadly features a non-metal deformable modulation element.

In general, in another aspect, the invention features a process for making cavity-type modulation elements by forming a sandwich of two layers and a sacrificial layer between them, the sacrificial layer having a thickness related to the final cavity dimension,

- 5 -

and using chemical (e.g., water) or a plasma based etch
process to remove the sacrificial layer.
          Among the advantages of the invention are the
following.
5   Very high-resolution, full-color images are
produced using relatively little power. The embodiment
which senses the image incident on the array has
relatively low noise. Their color response
characteristics are tunable by selection of the
10 dimensions of the antennas. The antenna or cavity
embodiments are useful in portable, low power, full color
displays, especially under high ambient light conditions.
Phase controlled reflective embodiments are useful in
passive light scanning such as optical disk readers
15 without moving parts. The emissive embodiments also
could be used as display devices especially in low-
ambient-light conditions.
          Because of the dielectric materials used in some
embodiments, the devices have the advantage of being
20 extremely light efficient, making them especially
appropriate for high intensity projection displays, and
reducing or eliminating the need for backlighting in low
ambient light applications. In addition, more accurate
color representations are possible, as well as designs
25 optimized for the IR and UV. Mechanical hysteresis
precludes the need for active drivers, and this coupled
with their geometric simplicity and monolithic nature
brings defect losses down significantly. The devices are
also exceptionally fast, low power, and non-polarizing.
30 The fact that they can be reflective and/or transmissive
enhances their flexibility.
          The process for fabrication as represented in some
embodiments relies on benign chemicals, minimizing waste
disposal problems, and facilitating the fabrication of
35 devices on a variety of substrates (e.g., plastics or

- 6 -

integrated circuits) using a larger variety of materials.
Devices on plastic substrates have the potential of being
extremely inexpensive. All of the manufacturing
technologies used are mature, further reducing
5 manufacturing costs.

Other advantages and features of the invention
will become apparent from the following description and
from the claims.

Description

10   Fig. 1 is a perspective view of a display device.

Fig. 2 is a perspective schematic exploded view of
a representative portion of the screen of Fig. 1.

Fig. 3 is an enlarged top view of a tri-dipole of
Fig. 2.

15   Fig. 4 is a schematic view of a single dipole
antenna of Fig. 3.

Fig. 5 is a schematic perspective view, broken
away, of a portion of the screen of Fig. 1.

Fig. 6 is an enlarged top view of an individual
20 tri-bus of Fig. 2.

Fig. 7 is an enlarged perspective view of a
representative portion of the screen of Fig. 1.

Fig. 8 is a cross-sectional view along 8-8 of Fig.
7.

25   Fig. 9 is a diagram of a portion of a control
circuit of Fig. 2, and a corresponding dipole antenna of
Fig. 3.

Figs. 10A, 10B, 10C are representative graphs of
the input voltage to the bias source of Fig. 9.

30   Fig. 11 is a diagram of portions of the control
modules for a row of pixels,

Fig. 12 is a circuit diagram of an oscillator.

Fig. 13 is a schematic diagram of a circuit module
of Fig. 2, a corresponding dipole antenna of Fig. 3, and

- 7 -

a graphical representation of the output of a binary counter.

Fig. 14 is a circuit diagram of the pulse counter of Fig. 13.

5   Figs. 15, 16, 17, 18, and 19 are top views of alternative dipole arrangements.

Figs. 20A through 20F are perspective views of a cavity devices.

Figs. 21A and 21B are side views of the cavity 10 device.

Figs. 22A through 22F are graphs of useful pairs of frequency responses which can be achieved by the cavity device when it is in one of two states.

Figs. 22G through 22AF are a larger list of graphs 15 of individual frequency responses which in some combinations prove useful in the cavity device.

Figs. 23A and 23B are top and cutaway side views respectively, of a display.

Figs. 23C and 23D are top and cutaway side views, 20 respectively, of another display.

Fig. 23E is a side view of another display configuration.

Fig. 24A is a graph of an electromechanical response of the cavity device.

25   Figs. 24B and 24C are graphs of addressing and modulation schemes for a display.

Fig. 24D is a graph of a hysteresis curve.

Figs. 25A through 25N and Figs 26A through 26K are perspective views of the device during assembly.

30   Figs. 27A through 27C are side views of dielectric mirrors.

Fig. 27D is a top view of a dielectric mirror.

Figs. 28A, 28B are perspective and top views of a linear tunable filter.

- 8 -

Figs. 29A, 29B are perspective and top views of a deformable mirror.

Referring to Fig. 1, device 20 includes a screen 22 for displaying or sensing a high resolution color
5 image (or a succession of color images) under control of power and control circuitry 26. The image is made up of a densely packed rectangular array of tiny individual picture elements (pixels) each having a specific hue and brightness corresponding to the part of the image
10 represented by the pixel. The pixel density of the image depends on the fabrication process used but could be on the order of 100,000 pixels per square centimeter.

Referring to Fig. 2, each pixel is generated by one so-called tri-dipole 30. The boundary of each tri-
15 dipole is T-shaped. The tri-dipoles are arranged in rows 32 in an interlocking fashion with the "Ts" of alternating tri-dipoles oriented in one direction and the "Ts" of intervening tri-dipoles along the same row oriented in the opposite direction. The rows together
20 form a two-dimensional rectangular array of tri-dipoles (corresponding to the array of pixels) that are arranged on a first, external layer 34 of screen 22. The array may be called an electrically alterable optical planar array, or a visible spectrum modulator array.

25   On a second, internal layer 36 of screen 22 so-called tri-busses 38 (shown as T-shaped blocks in Fig. 2) are arranged in an interlocking two-dimensional array 40 corresponding to the layout of the tri-dipoles on layer 34 above. Each tri-dipole 30 is connected to its
30 corresponding tri-bus 38 by a multi-conductor link 42 running from layer 34 to layer 36 in a manner described below.

On a third, base layer 44 of screen 22 a set of circuit modules 46 are arranged in a two-dimensional

- 9 -

rectangular array corresponding to the layouts of the
tri-dipoles and tri-busses. Each circuit module 46 is
connected to its corresponding tri-bus 38 by a six-
conductor link 48 running from layer 36 to layer 44 in a
5 manner described below.

    Each circuit module 46 electronically controls the
optical characteristics of all of the antennas of its
corresponding tri-dipole 30 to generate the corresponding
pixel of the image on screen 22. Circuit modules 46 are
10 connected, via conductors 50 running along layer 44, to
an edge of layer 44. Wires 52 connect the conductors 50
to control and power circuitry 26 which coordinates all
of the circuit modules 46 to 25 generate the entire
image.

15   Referring to Fig. 3, each tri-dipole 30 has three
dipole sections 60, 62, 64. The center points 59, 61, 63
of the three sections are arranged at 120 degree
intervals about a point 65 at the center of tri-dipole
30. Each section 60, 62, 64 consists of a column of
20 dipole antennas 66, 68, 70, respectively, only ten dipole
antennas are shown in each section in Fig. 3, but the
number could be larger or smaller and would depend on,
e.g., the density with which control circuits 46 can be
fabricated, the tradeoff between bandwidth and gain
25 implied by the spacing of the antennas, and the resistive
losses of the conductors that connect the antennas to the
control circuit 46. Only the two arms of each dipole
antenna are exposed on layer 34, as shown in Fig. 3. The
dipole antennas of a given section all have the same
30 dimensions corresponding to a particular resonant
wavelength (color) assigned to that section. The
resonant wavelengths for the three sections 60, 62, 64
are respectively 0.45 microns (blue), 0.53 microns
(green), and 0.6 microns (red).

- 10 -

Referring to Fig. 4, each dipole antenna 80
schematically includes two Ls 82, 84 respectively made up
of bases 86, 88, and arms 90, 92. The bases of each
antenna 80 are electrically connected to the

5 corresponding circuit module 46. The span (X) of arms
90, 92 is determined by the desired resonant wavelength
of dipole antenna 80; for example, for a resonant
wavelength of lambda, X would be lambda/2. Dipole
antennas 66, 68, 70 have X dimensions of 0.225 microns

10 (lambda$_1$,/2), 0.265 microns (lambda$_2$/2), and 0.3 microns
(lambda$_3$,/2), respectively. The effective length (Y) of
bases 86, 88 from arms 90, 92 to circuit module 46 is
also a function of the dipole antenna's resonant
wavelength; for a resonant wavelength of lambda, Y is a

15 multiple of lambda.

Referring to Fig. 5, each of the bases 86, 88
physically is made up of four segments; (1) one of the
conductors 96 of link 42, (2) a portion 112 of tri-bus
38, (3) a short connecting portion 124 of tri-bus 38, and

20 (4) one of the conductors 94 of link 48, which together
define a path (e.g., the path shown as dashed line 97)
with an effective length of Y from the arm (e.g., 92) to
the circuit module 46.

The placement of link 42 perpendicular to the

25 surface of layer 34 allows arms 90, 92 (formed on the
surface of layer 34) to be spaced at an actual spacing Z
that is closer than lambda/2, the minimum required
effective Y dimension of bases 86, 88. Spacing Z may be
chosen based on the bandwidth/gain tradeoff, and for

30 example may be one quarter of the resonant wavelength for
the dipole antennas of a given section (i.e., lambda/4,
or 0.1125 microns (lambda$_1$/4), 0.1325 microns (lambda$_2$/4)
and 0.15 microns (lambda$_3$/4) for antennas 66, 68, 70,
respectively).

- 11 -

Referring to Fig. 6, each tri-bus 38 is formed of
aluminum on layer 36 and has three zigzag shaped bus
pairs 100, 102, 104 for respectively connecting dipole
antennas of the corresponding sections 60, 62, 64 of tri-
5 dipole 30. Bus pairs 100, 102, 104 are connected to
individual dipole antennas 66, 68, 70 via conductors of
link 42 (Fig. 2) that are joined to the bus pairs at
points, e.g., 106.

Each bus pair 100, 102, 104 has two parallel buses
10 108, 110. Bus 108 electrically connects together the
arms of the dipole antenna 5 of the corresponding section
and, independently, the related bus 110 electrically
connects together the arms 92 of the dipole antennas of
that same section.

15   Points 106 delineate a series of fragments 112,
114, 116 on each of the three bus pairs 100, 102, 104,
respectively. Each fragment forms part of one or more of
the bases 86, or 88 and therefore contributes to the
effective Y dimension.

20   The lengths (Q) of fragments 112, 114, 116 are
one-half of the resonant wavelengths (i.e. lambda/2) of
the sections 60, 62, 64, or 0.225 microns (lambda$_1$,/2),
0.265 microns (lambda$_2$,/2), and 0.3 microns (lambda$_3$,/2),
respectively.

25   The conductors of link 48 (Fig. 2) are attached to
tri-bus 38 at points 118, 120, 122 at the ends of buses
108, 110. Between points 118, 120, 122 and the first
points 106 on along buses 108, 110 are fragments 124,
126, 128, which also form portions of the bases 86, 88
30 and are included to adjust the effective Y dimensions of
those bases to be integer multiples of lambda/2. The
lengths of the three fragments 124, 126, 128 are 0.1125
microns, 0.1525 microns, and 0.1875 microns,
respectively.

- 12 -

Referring to Fig. 7, each dipole antenna 80 is
physically formed (of aluminum) on an insulating
semiconductor (e.g. silicon dioxide of silicon nitride)
substrate 130 (part of layer 34) by x-ray or electron
5 beam lithography or other technique suitable for forming
submicron-sized structures.

Tri-busses 38 (not seen in Fig. 7) are formed
on the upper-side of a second insulating semiconductor
substrate 132 (part of layer 36). Circuit modules 46
10 (not seen in Fig. 7) are part of a third insulating
semiconductor substrate 134 (part of layer 44) and are
connected by conductors 50 to gold contact pads 136 (only
one shown, not to scale) formed on the edge of substrate
layer 134.

15 Referring to Fig. 8, circuit module 46 is formed
in and on substrate 134 by any one of several monolithic
processes. A section 138 of the substrate 134, which has
been previously coated with an insulating semiconductor
oxide layer 140, is repeatedly masked (whereby small
20 windows are opened in the oxide layer, exposing the
semiconductor beneath) and exposed to n and p dopants to
form the desired circuit elements (not shown in detail in
Fig. 8).

The individual circuit elements are connected to
25 each other and to external contact pad 136 (Fig. 7) by
aluminum conductors 142, 50, respectively. To form the
connections, holes 144 are opened in oxide layer 140 and
a sheet of aluminum is deposited, filling holes 144.
Using a masking technique similar to the one described
30 above the unwanted aluminum is removed, leaving only
conductors 142, 50.

Semiconductor substrate layer 132 is deposited
directly on top of the remaining exposed oxide layer 140
and conductors 142, 50. Holes 146 (one shown) (opened
35 using a suitable lithographic technique) are channels for

- 13 -

the electrical conductors 147 of links 48, which connect
tri-bus 38 and circuit module 46. Tri-bus 38 is etched
from a sheet of aluminum deposited onto the surface of
layer 132. The deposition process fills holes 146,
5 thereby forming the conductors of links 48.

Substrate layer 130 is deposited onto the surface
of substrate layer 132 and tri-bus 38. The arms of
dipole antennas 80 are formed by depositing a sheet of
aluminum onto the surface of layer 130 and etching away
10 the unwanted metal. During the deposition process holes
148 are filled thereby forming the conductors 149 of
links 42 between the arms of dipole antenna 80 and tri-
bus 38.

The conductors 149 are the uppermost parts of
15 bases 86, 88 (Fig. 4) of dipole antennas 66, 68, 70; the
lengths of conductors 149 together with the lengths of
fragments 112, 114, 116 (Fig. 6), the lengths of
fragments 124, 126, 128, and the lengths of the
conductors 147 determine the effective Y dimension of
20 bases 86, 88.

The length of the conductors 149 is determined by
the thickness of the substrate 130 through which links 42
pass. Substrate 130 and links 42 are 0.05625 microns
(i.e. $lambda_1$,/8) thick. This thickness is achieved by
25 controlling the deposition rate of the semiconductor
material as layer 130 is formed.

The length of the conductors 149 is determined by
the thickness of the substrate layer 132 through which
they pass. This,layer and links 48 are therefore also
30 0.05625 microns 20 thick.

The Y dimensions for the dipole antennas 66, 68,
70 of sections 60, 62, 64 therefore are as follows:

(a) For section 60, Y equals the sum of 0.05625
microns (length of the conductor in link 42, $lambda_1/8$) +
35 n * 0.225 microns (where 0.225 microns = $lambda_2/2$, the

- 14 -

length of a fragment 112, and n = the number of fragments
112 in each base 86, 88 of the nth dipole antenna 66n) +
0.1125 microns (length of fragment 124, $lambda_1/4$) +
0.05625 microns (length of the conductor in link 48,
5 $lambda_1/8$), and that sum equals (n + 1) * ($lambda_1/2$).

　　　　(b) For section 62, Y equals the sum of 0.05625
microns (length of link 42, $lambda_1/8$) + n * 0.265
microns (where 0.265 microns = $lambda_2/2$, the length of a
fragment 114, and n = the number of fragments 114 in each
10 base 86, 88 of the nth dipole antenna 68n) + 0.1125
microns (length of fragment 126, ($lambda_2/2$) -
($lambda_1/4$)) + 0.05625 microns (length of the conductor
in link 48, $lambda_1/8$), and that sum equals (n +
1)*($lambda_1/2$).

15　　　　(c) For section 64, Y equals the sum of 0,05625
microns (length of conductor in link 42, $lambda_1/8$) + n *
0.3 microns (where 0.3 microns - $lambda_3/2$, the length of
a fragment 116, and n equals the number of fragments 116
in each base 86, 88 of the nth dipole antenna 70n) +
20 0.1875 microns (the length of fragment 128, ($lambda_3/2$) -
($lambda_1/4$)) + 0.05625 microns (length of conductor in
link 48), and that sum equals (n + 1) * ($lambda_3/2$).

　　　　Referring again to Fig. 1, in some embodiments,
the displayed image is not emitted from device 20 but is
25 comprised of ambient light (or light from a source, not
25 shown) selectively reflected by the tri-dipoles 30 of
screen 22.

　　　　In that case, each tri-dipole 30 receives ambient
light having a broad spectrum of wavelengths and is
30 controlled by the corresponding circuit module to reflect
only that portion of the ambient light manifesting the
hue and brightness of the desired corresponding pixel.

　　　　The hue generated by tri-dipole 30 depends on the
relative intensities of the light reflected by sections
35 60, 62, 64. The overall brightness of that hue of light

- 15 -

in turn depends on the absolute intensities of the light
radiation reflected by sections 60, 62, 64. Thus, both
the hue and brightness of the light generated by tri-
dipole 30 can be controlled by regulating the intensity
5 of the light reflected by the dipole antennas in each
section of the tri-dipole; this is done by controlling
the reflectivity of each dipole antenna, i.e.. the
percentage of the light of the relevant wavelength for
that dipole antenna which is reflected.

10   The desired percentage is attained not by
regulating the amount of light reflected at any given
instant but by arranging for the antenna to be fully
reflective in each of a series of spaced apart time
slots, and otherwise non-reflective. Each dipole
15 antenna, in conjunction with its circuit module, has only
two possible states: either it reflects all of the light
(at the antenna's resonant frequency), or it reflects
none of that light. The intensity is regulated by
controlling the percentage of total time occupied by the
20 time slots in which the dipole antenna occupies the first
state.

        Each dipole antenna is controlled to be reflective
or not by controlling the impedance of the dipole antenna
relative to the impedance of the medium (e.g., air)
25 through which the light travels. If the medium has an
effective impedance of zero, then the relationship of the
reflectivity of the dipole antenna to zero (the
controlled impedance of the dipole antenna) can be
derived as follows. If we define a three-axis system x-
30 y-z in which the x and y axes are in the plane of the
array and the z axis is the axis of propagation of the
incident and reflected waves, where z = 0 is the surface
of the array, then the incident plus reflected wave for z
< 0 may be represented as:

- 16 -

$$\overline{E} = \hat{x}E_0 e^{-jkz} + \hat{x}E_r e^{+jkz} \qquad (1)$$

$$\overline{H} = \frac{V \times \overline{E}}{-j\omega\mu_0} = \hat{y}\frac{1}{\eta_0}[E_0 e^{-jkz} - E_r e^{+jkz}] \qquad (2)$$

where $\underline{E}$ (overbar) is the complex amplitude of the
electric field of the sum of the transmitted wave and the
reflected wave; $\underline{E}_0$ is the complex amplitude of the
electric field of the transmitted 20 wave; $\underline{E}_r$, is the
5 complex amplitude of the electric field of the reflective
wave; x(hat) is the orientation of the electric field of
the wave; $\underline{H}$ is the amplitude of the magnetic field;
y(hat) is the orientation of the magnetic field; μo is
the permeability of free space; ϵ_0 is the permittivity of
10 free space; k = ωsqrt$[\mu_0\epsilon_0]$ is the wavenumber; and η =
sqrt $[\mu_0/\epsilon_0]$ is the impedance of free space. For z > 0
(i.e.., within free space) only the transmitted wave
exists and is represented by

$$\overline{E} = \hat{x}E_t e^{-jk_t z} \qquad (3)$$

$$\overline{H} = \hat{y}\frac{1}{\eta_t}E_t e^{-jk_t z} \qquad (4)$$

$\underline{E}$(overbar) is the complex amplitude the transmitted wave
15 at z = 0, k_t = sqrt $[\mu\epsilon]$ is its wavenumber; η = sqrt
$[\mu/\epsilon]$ is the impedance of the medium, i.e. z > 0.
Boundary conditions (z = 0) for tangential electric
fields are imposed on equations 1 and 2 and they are
combined to yield,

$$\hat{x}[E_0 + E_r] = \hat{x}E_t \qquad (5)$$

20 In the same way, continuity for tangential magnetic
fields (z = 0) at the boundary yields,
Dividing equations 5 and 6 by $\underline{E}_0$, and $\underline{E}_0/\eta_0$ respectively
gives the following two equations:

- 17 -

$$\mathcal{P}(1/\eta_0)(E_0 - E_R) = \mathcal{P}(1/\eta_t)E_t \qquad (6)$$

$$1 + E_r/E_0 = E_t/E_0 \qquad (7)$$

$$1 - E_R/E_0 = (\eta_0/\eta_t)(E_t/E_0) \qquad (8)$$

E_r/E_0 is called Γ and is the complex reflection coefficient while $E_t/\eta_0 = T$ is called the complex transmission coefficient, and $\eta_t/\eta_0 = \eta_n$ is the normalized wave impedance. Solving for T and Γ yields

$$T = \frac{E_t}{E_0} = \frac{2}{1 + \eta_0/\eta_t} = \frac{2\eta_n}{\eta_n + 1} \qquad (9)$$

$$\Gamma = \frac{E_R}{E_0} = T - 1 = \frac{\eta_N - 1}{\eta_n + 1} \qquad (10)$$

5   For matched impedance values, $\eta_0 = \eta_n$, the reflection
    coefficient is zero, and T = 1 (i.e.., no reflection),
    and in the case of a load at the boundary, a matched
    antenna, there is complete absorption.
         As η_n approaches zero or infinity, the
10 reflection coefficient approaches plus or minus one,
    implying total reflection.
         Referring to Fig. 9, the impedance z_L, of dipole
    antenna 80 is controlled by a variable resistance PIN
    diode 160 connected across bases 86, 88. PIN line 162 to
15 the output of a bias high voltage or a low voltage based
    on a line 168 from power and the output of bias source
    164 is a high voltage, the resistance R of PIN diode 160
    (and hence the impedance (E,) of the dipole antenna is
    zero causing full reflection; when the output of bias
20 source 164 is a low voltage 98, resistance R is set to a
    value such that the resulting impedance z@ is matched to
    z. (the impedance of the air surrounding the antenna),
    causing zero reflection.

- 18 -

To generate an entire image on screen 20, power
and control circuitry 26 receives a video signal (e.g. a
digitized standard RGB television signal) and uses
conventional techniques to deliver corresponding signals
5 to modules 46 which indicate the relative desired
intensities of light reflected from all sections 60, 62,
64 of all of the tri-dipoles in the array at a given
time. Circuit modules 46 use conventional techniques to
deliver an appropriate stream of input control signal
10 pulses to each bias source 164 on line 168.

The pulse stream on each line 168 has a duty cycle
appropriate to achieve the proper percentages of
reflectance for the three Sections of each tri-dipole.
Referring to Figs. 10A, 10B, and 10C, for example, pulse
15 stream 170 has a period T and a 50% duty cycle. For the
first 50% of each period T the input to bias source 164
is high and the Corresponding output of source 164 is a
high voltage. During this portion of the cycle dipole
antenna 80 will reflect all received light having the
20 dipole antenna's resonant wavelength. For the second 50%
of the cycle the output of source 164 will be low and
dipole antennas 80 will absorb the received light. In
Figs. 10B, 10C, pulse streams 172, 174 represent a 30%
duty cycle and a 100% duty cycle respectively; with a 30%
25 duty cycle the effective intensity of the light radiation
of the dipole antennas of the section will be 30%; for a
duty cycle of 100%, the effective intensity is 100%.

For example, if a particular pixel of the image is
to be brown, the relative intensities required of the
30 three red, 25 green, and blue sections 60, 62, 64 may be,
respectively, 30, 40, and 10. The input signals to the
bias sources 164, carried on lines 168, would then have
duty cycles, respectively, of 30%, 40%, and 10%. An
adjacent pixel which is to be a brown of the same hue but

- 19 -

greater brightness might require duty cycles of 45%, 60%, and 15%.

Referring to Fig. 11, to accomplish the delivery of the pulse width modulated signals from circuitry 26 to
5 the pixel circuit modules 46, each circuit module 46 in the row includes storage 180, 182 for two bits. The bit 1 storage elements 180 of the modules 46 in the row are connected together to create one long shift register with the pulse width modulated signals being passed along the
10 row data line 184 from pixel to pixel. If, for example, the period of the modulated signals is 1 millisecond and there are ten different intensity levels, then an entire string of bits (representing the on or off state of the respective pixels in the row during the succeeding 1/10
15 millisecond) is shifted down the row every 1/10 millisecond. At the end of the initial 1/10 millisecond all of the bits in elements 180 are shifted to the associated elements 182 by a strobe Pulse on strobe line 186. The content of each element 182 is the input to the
20 driver 188 for the appropriate one of the three colors of that pixel, which in turn drives the corresponding section 60, 62, 64 of the tri-dipole. The rate at which data is shifted along the shift registers is determined by the number of elements on a given row, the number of
25 rows, the number of intensity levels, and the refresh rate of the entire array.

In another embodiment, the light comprising the image is emitted by tri-dipoles 30 rather than being produced by reflected ambient light. In that case, each
30 tri-dipole generates the light for a single pixel with a hue and brightness governed by the intensities of the light emitted by each of the three sections 60, 62, 64.

Each dipole antenna within a tri-dipole is caused to emit light at the resonant wavelength of that antenna
35 by stimulating it using a signal whose frequency

- 20 -

corresponds to the resonant wavelength. Thus, the
sections 60, 62, 64 will emit blue (lambda$_1$), green
(lambda$_2$), and red (lambda$_3$) light respectively when
provided with signals whose frequencies equal,
5 respectively, lambda$_1$, lambda$_2$ and lambda$_3$.

For an idealized dipole, the current $\underline{I}$ and current
density $\underline{J}$(overbar)(r'overbar) are described by

$$I = j\omega q \tag{11}$$

$$\underline{J}(\overline{r}') = \hat{z}Id\delta(\overline{r}') \tag{12}$$

where $\underline{q}$ is the charge density; z(hat) indicates the
direction of the current (along the z-axis); ω is angular
10 frequency; and d is the distance between ideal point
charges representing the dipole. The vector potential
$\underline{A}$(overbar) in polar coordinates is given by

$$\begin{aligned}\overline{A} &= \hat{r}A_r + \hat{\theta}A_\theta \\ &= (\hat{r}\cos\theta - \hat{\theta}\sin\theta)\frac{\mu_o Id}{4\pi r}e^{-jkr}\end{aligned} \tag{13}$$

where θ represents the angle relative to the dipole;
θ(hat) is the angular orientation of the wave; μ_0 is the
15 permeability of free space; r is radius from the dipole;
r(hat) is radial orientation of the wave; A_r is the
radial component of the vector potential; A_θ is the
angular component of the vector potential; and k is a
factor which is used to represent sinusoidally varying
20 waves. The H field is given by

$$\begin{aligned}\overline{H} &= \hat{\varphi}\frac{1}{\mu_o r}[\frac{\delta}{\delta\theta}(rA_\theta - \frac{\delta}{\delta\theta}(A_r)] \\ &= \hat{\varphi}\frac{jkId}{4\pi r}e^{-jkr}[1+\frac{1}{jkr}]\sin\theta\end{aligned} \tag{14}$$

where φ is elevation, with respect to the dipole. The E
field is given by,
The far-field equation is given by

- 21 -

$$\bar{E} = \frac{1}{j\omega\epsilon_0}\nabla\times\bar{H}$$

$$= \sqrt{\mu_0/\epsilon_0}\frac{jkId}{4\pi r}e^{-jkr}(\hat{r}[\frac{1}{jkr}+(\frac{1}{jkr})^2]2\cos\theta \qquad (15)$$

$$+\hat{\theta}[1+\frac{1}{jkr}+(\frac{1}{jkr})^2]\sin\theta)$$

$$\bar{H} = \hat{\phi}\frac{jkId}{4\pi r}e^{-jkr}\sin\theta$$

$$\bar{E} = \hat{\theta}\sqrt{\mu_0/\epsilon_0}\frac{jkId}{4\pi r}e^{-jkr}\sin\theta \qquad (16)$$

Equation (16) describes the radiation pattern away from a dipole antenna at distances significantly greater than the wavelength of the emitted electromagnetic wave. It is a very broad radiation pattern providing a wide
5 field of view at relevant distances.

Referring to Fig. 12, the dipole antennas 66, 68, 70 of each section 60, 62, 64 are driven by signals (e.g., sinusoidal) with frequencies of 5×10^{14} Hz, 5.6×10^{14} Hz, and 6.6×10^{14} Hz for red, green, and blue,
10 respectively. These signals are supplied by three monolithic oscillators 200 (one shown) within circuit module 46, each tuned to one of the three required frequencies.

In circuit 200 (an a stable multivibrator), the
15 center pair of coupled transistors 202, 204 are the primary active elements and will oscillate if the circuit admittance's are set appropriately. Diodes 206, 208, 210, 212 provide coupling capacitance's between the transistors and the inductors 214, 216 are used to tune
20 the operating frequency.

In a third embodiment, an image of the object is focused by a conventional lens (not shown in Fig. 1) onto screen 22, which then acts as an image sensor. The tri-dipoles of screen 22, controlled by power and control
25 circuitry 26, generate electrical signals corresponding

- 22 -

to pixels of the received image. The signals are then
processed by a processor which, in conventional fashion,
delivers a derived RGB video signal which can then be
transmitted or stored.

5   The signals generated for each tri-dipole are
generated by the corresponding circuit module 46 and
represent the hue and brightness of the light radiation
received at that tri-dipole.

        Each section of tri-dipole 30 can only be used
10 to measure light having the resonant wavelength of its
respective dipole antennas, however, because most colors
can be expressed as a combination of red, green, and
blue, circuit module 46 can, by independently measuring
the intensity of the light radiation received at each
15 section 60, 62, 64, derive a signal which specifies the
hue and intensity of the received pixel.

        Referring to Fig. 13, dipole antenna 80 will
absorb incident light radiation at its resonant
wavelength when its reflection coefficient (Γ_L) is zero,
20 which occurs when its controlled impedance (z_L) matches
the impedance of the medium (z_0). In those
circumstances, a voltage pulse is produced across the
ends 308, 310 of dipole 80 for each incident photon. The
relative magnitude of the light radiation received by
25 each dipole antenna can thus be measured by counting the
average number of pulses across ends 308, 310 over a
given time period.

        In this embodiment, circuit module 46 includes a
terminating load resistor 315 connected across ends 308,
30 310. The controlled impedance of the combination of
dipole antenna 80 and resistor 315, described by the
equations set forth below, is equal to z_0.

        The voltage of the pulse across resistor 315
(created by an incident photon) is illustrated by the

- 23 -

sine wave graph above register 15 and is described
generally by the following equation

$$V(z) = \underline{V} + e^{-jkz} + \Gamma_L e^{jkz} \qquad (17)$$

Because $z_L = z_0$, $\Gamma_L = 0$, and equation 17 simplifies to

$$V(z) = \underline{V} + e^{-jkz} \qquad (18)$$

A pulse detector 318 amplifies and sharpens the
5   resulting pulse to a square wave form as shown, which is
then used as the clock (CLK) input 319 to a binary
counter 320. The output of the binary counter is sampled
at a regular rate; collectively the samples form a
digital signal representing the intensity of received
10   light radiation over time. Each time counter 320 is
sampled, it is reset to zero by a pulse on control line
322, Counter 320 thus serves as a digital integrator that
indicates how much light arrived in each one of a
succession of equal length time periods.
15   Referring to Fig. 14, in pulse detector 318 the
pair of transistors 322, 324 serve as a high impedance
differential stage whose output (representing the voltage
difference between points 308, 310) is delivered to an
amplifier 326. Amplifier 326 serves as a high-bandwidth
20   gain stage and delivers a single sided output pulse to a
conditioning circuit 328 that converts slow rising pulses
to square pulses 330 for driving counter 320.
In another embodiment, the array of tri-dipoles is
operated as a phased array. The operation of phased
25   arrays is discussed more fully in Amitay, et al., <u>Theory
and Analysis of Phased Array Antennas</u>, 1972, incorporated
herein by reference. By controlling the spacing of
successive tri-dipoles across the array and the relative
phases of their operation, wave cancellation or
30   reinforcement can be used to control the direction in
three dimensions and orientation of the radiation. Beams

- 24 -

can thus be generated or scanned. In the case of an
array used to sense incoming radiation, the array can be
made more sensitive to radiation received from selected
directions.

5   Other embodiments are also possible. For example,
referring to Fig. 15, each section of tri-dipole 400
array be a single dipole antenna 406, 407, 408. The tri-
dipole antennas are then arranged about a center Point
410 at 120 degree intervals in a radial pattern. Bases
10 411, 412, as well as arms 414, 415, of the dipole
antennas, are all formed on the same surface.

           Referring to Fig. 16, each section may consist of
multiple dipole antennas 406, 407, 408 connected by
attaching the bases 411, 412 of each succeeding dipole
15 antenna to the inner ends of arms 414, 415 of the
preceding dipole antenna. Circuit modules 416 are formed
on the surface of layer 413.

           Referring to Fig. 17, a multi-dipole 430 could
have five sections 432, 434, 436, 438, 440 composed of
20 dipole antennas 442, 444, 446, 448, 450, respectively.
The dipole antennas of the different sections would have
different resonant wavelengths. Other multi-dipoles
might have any number of sections.

           The scanning of pixels could be done other than by
25 pulse width modulation, for example, using charge coupled
devices to shift packets of charge along the rows of
pixels.

           Referring to Figs. 18, 19, other arrangements of
dipole antennas may be used in order to match the area
30 required for the control circuit modules.

           Referring to Fig. 18, each section 470 of a tri-
dipole in the reflective mode could be formed of a number
of subsections (e.g., 472) arranged in two rows 474 and a
number of columns 47. The antennas 478 in each
35 subsection 472 are all served by a single PIN diode

- 25 -

circuit 480 located at the peripheral edge of section 470
at the end of the subsection on the layer below the
antenna layer. All circuits 480 for the entire Section
470 are in turn served by a single bias source 164 (Fig.
5 9). This arrangement reduces the number of bias sources
required for the entire array of tri-dipoles. Fig. 19
shows an alternate arrangement in which there is but one
row of subsections each served by a single PIN diode
circuit at the end of the row.

10   In order to reduce the number of conductors 50,
selected tri-dipoles could be used to receive control
signals transmitted directly by light and to pass those
control signals to the control circuits of nearby active
tri-dipoles.

15   The dipoles could be mono-dipoles comprised of
only a single dipole antenna, all with the same resonant
wavelength.

        Dipole antennas 470 could be randomly arranged on
the surface of layer 472 of screen 22.

20   A different color regime, e.g. cyan-magenta-
yellow, could be substituted for RGB.

        Spiral, biconical, slotted, and other antenna
configurations could be substituted for the dipole
configuration.

25   The array could be three-dimensional.

        The successive tri-dipoles in the array can be
oriented so that their respective antennas are orthogonal
to each other to enable the array to interact with
radiation of any arbitrary polarization.

30   The PIN diodes could be replaced by other
impedance controlling elements. Such elements might
include quantum well transistors, superconducting
junctions, or transistors based on vacuum
microelectronics. Further improvement could be achieved
35 by reducing the complexity of the third layer containing

- 26 -

control circuitry. The electronics required to get
control signals to the circuitry could be eliminated by
the use of laser or electron beams to provide such
signals. This would have the advantage of allowing for
5 arrays of even higher density.

The array could be fabricated on a transparent
substrate, thus facilitating transmissive operation.

In other embodiments, the antenna arrays alone
(without control circuitry or connection buses) may be
10 fabricated on one-half of a microfabricated
interferometric cavity. The antenna array can be
considered a frequency selective mirror whose spectral
characteristics are controlled by the dimensions of the
antennas. Such a cavity will transmit and reflect
15 certain portions of incident electromagnetic radiation
depending on (a) the dimensions of the cavity itself and
(b) the frequency response of the mirrors. The behavior
of interferometric cavities and dielectric mirrors is
discussed more fully in Macleod, H. A.,   Thin Film
20 Optical Filters, 1969, incorporated by reference.

Referring to Fig. 20a, two example adjacent
elements of a larger array of this kind include two
cavities 498, 499 fabricated on a transparent substrate
500. A layer 502, the primary mirror/conductor, is
25 comprised of a transparent conductive coating upon which
a dielectric or metallic mirror has been fabricated.
Insulating supports 504 hold up a second transparent
conducting membrane 506. Each array element has an
antenna array 508 formed on the membrane 506. The two
30 structures, 506 and 508, together comprise the secondary
mirror/conductor. Conversely, the antenna array may be
fabricated as part of the primary mirror/conductor.
Secondary mirror/conductor 506/508 forms a flexible
membrane, fabricated such that it is under tensile stress

- 27 -

and thus parallel to the substrate, in the undriven
state.

Because layers 506 and 502 are parallel, radiation
which enters any of the cavities from above or below the
5 array can undergo multiple reflections within the cavity,
resulting in optical interference. Depending on the
dimensions of the antenna array, as explained above, the
interference will determine its effective impedance, and
thus its reflective and/or transmissive characteristics.
10 Changing one of the dimensions, in this case the cavity
height (i.e., the spacing between the inner walls of
layers 502, 506), will alter the optical characteristics.
The change in height is achieved by applying a voltage
across the two layers at the cavity, which, due to
15 electrostatic forces, causes layer 506 to collapse.
Cavity 498 is shown collapsed (7 volts applied), while
cavity 499 is shown uncollapsed (0 volts applied).

In another embodiment, Fig. 20b, each cavity may
be formed by a combination of dielectric or metallic
20 mirrors on the two layers, and without the antennas
formed on either layer. In this case the spectral
characteristics of the mirror are determined by the
nature and thickness(es) of the materials comprising it.

In an alternative fabrication scheme, Fig. 20c,
25 each cavity is fabricated using a simpler process which
precludes the need for separately defined support
pillars. Here, each secondary mirror/conductor, 506, is
formed in a U-shape with the legs attached to the primary
layer; each secondary mirror/conductor thus is self-
30 supporting.

In yet another scheme, Fig. 20d, the cavity has
been modified to alter it's mechanical behavior. In this
version, a stiffening layer, 510, has been added to limit
deformation of the membrane while in the driven state.
35 This assures that the two mirrors will remain parallel as

- 28 -

a driving voltage is gradually increased. The resulting
device can be driven in analog mode (e.g., cavity 511 may
be driven by 5 volts to achieve partial deformation of
the cavity) so that continuous variation of its spectral
5 characteristics may be achieved.

Figure 20E illustrates an additional
configuration. In this scheme a stop layer 512 has been
added so that the position of the membrane 506 in the
driven state may be a fixed offset from the wall 502.
10 Alternative optical, electrical, or mechanical responses
may be accommodated in this fashion. For example, the
stop layer may act as an insulator between walls 506 and
502, or its thickness may be set to achieve a certain
center frequency when the device is driven.
15   Figure 20F shows an encapsulated version of the
device of the cavity. Encapsulation membrane 514 is
fabricated in the same fashion and using similar
materials as the original cavity, 502 and 506 by use of
the described processes. In this case, the process is
20 used to build structures on top of an array of cavities
which have already been fabricated. Encapsulation
membrane 514 is a continuous structure designed to be
rigid and inflexible. The function of this encapsulation
is multifold. First it acts as a hermetic seal so that
25 the entire array can be purged with an inert gas and
maintained at an appropriate pressure. Second, the
electrical and optical properties may also be useful in
the overall operation of the array. Using electrically
conducting materials, a voltage may be applied to
30 encapsulation membrane 514, and the resulting
electrostatic forces between membranes 514 and 506 can
alter the hysteresis of the underlying cavity in a useful
fashion. The collapse and release thresholds can be
modified beyond what is dictated by the structure of the
35 cavity itself. The electrostatic forces may also aid in